

## **Reliability Qualification Report**

### SGA-5263Z

Products Qualified by Similarity

SGA-4563Z/4463Z/4363Z/4263Z/4163Z SGA-3563Z/3463Z/3363Z/3263Z SGA-2463Z/2363Z/2263Z/2163Z SGA-1263Z/1163Z SGA-0363Z/0163Z SGA-8343Z/8543Z SGL-0263Z/0163Z

303 S. Technology Ct, Broomfield CO, 80021

Phone: (800) SMI-MMIC

http://www.sirenza.com Document RQR-103792 Rev B





#### I. Qualification Overview

The SGA-5263Z family of products has demonstrated reliable operation by passing all qualification testing in our product qualification test plan. The "Z' designates a lead-free lead frame using Tin plated leads and Green mold compound. The SGA-5263Z has been subject to stresses such as humidity (autoclave), extreme hot and cold environments (temperature cycling), moisture sensitivity (MSL-1 and solder reflow testing), and has demonstrated reliable performance.

#### **II. Introduction**

Sirenza Microdevices' SGA-5263Z is a high performance cascadeable 50-ohm amplifier designed for operation at voltages as low as 3.4V. This RFIC uses the latest Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process featuring 1 micron emitters with  $F_T$  up to 50GHz. This circuit uses a Darlington pair topology with resistive feedback for broadband performance as well as stability over its entire temperature range. Internally matched to 50 Ohm impedance, the SGA-5263Z requires only DC blocking and bypass capacitors for external components.

#### **III. Fabrication Technology**

These amplifiers are manufactured using a Silicon Germanium Heterojunction Bipolar Transistor (HBT) technology. This self-aligned emitter, double poly HBT process has been in production by our foundry since 1998. The process has been successfully used for a wide range of RFIC products including GSM PAs, DECT front end transceivers, LNAs & VCOs. This process offers comparable performance to GaAs HBTs with the added advantages of mature and high producible Silicon wafer processing.

#### IV. Package Type

The SGA-5263Z power amplifier is packaged in a plastic encapsulated SOT-363 package that is assembled using a highly reproducible automated assembly process. The die is mounted using an industry standard thermally and electrically conductive silver epoxy. The SOT-363 is a similar package differing only by having two more leads than the SOT-343.

Figure 1: Image of SOT-363 Encapsulated Plastic Package (left) and a SOT-343 Encapsulated Plastic Package (right)







#### V. Qualification Methodology

The Sirenza Microdevices qualification process consists of a series of tests designed to stress various potential failure mechanisms. This testing is performed to ensure that Sirenza Microdevices products are robust against potential failure modes that could arise from the various die and package failure mechanisms stressed. The qualification testing is based on JEDEC test methods common to the semiconductor industry. A FMEA approach is used to determine the test methods to be included in the qualification plan. The manufacturing test specifications are used as the PASS/FAIL criteria for initial and final DC/RF tests.

#### VI. Qualification By Similarity

A device can be qualified by similarity provided that no new potential failure modes/mechanisms are possible in the new design. Products qualified by similarity listed on Page 1 of this document.

#### VII. Operational Life Testing

Sirenza Microdevices defines operational life testing as a DC biased elevated temperature test performed at the maximum <u>operational</u> junction temperature limit. For the SGA-5263Z the maximum operational temperature limit is 150°C. The purpose of the operational life test is to statistically show that the product operated at its maximum operational ratings will be reliable by operating several hundred devices for a total time of 1000 hours. The results for this test are expressed in device hours that are calculated by multiplying the total number of devices passing the test by the number of hours tested.

#### VIII. Moisture Sensitivity Level - MSL Level 1 Device

SGA-5263Z has successfully completed 168 hours of moisture soak (85°C/85%RH) followed by three convection reflow cycles with a peak temperature of 270°C. The successful completion of this test classifies the part as JESD 22-A113B Moisture Sensitivity Level 1 (MSL-1). MSL-1 indicates that no special dry pack requirements or time limits from opening of static bag to reflow exist for the SGA-5263Z. MSL-1 is highest level of moisture resistance that a device can be classified according to the above mentioned standard.





#### IX. Electrostatic Discharge Classification

Sirenza Microdevices classifies Human Body Model (HBM) electrostatic discharge (ESD) according to the JESD22-A114 convention. All pin pair combinations were tested. Each pin pair is stressed at one static voltage level using 1 positive and 1 negative pulse polarity to determine the weakest pin pair combination. The weakest pin pair is tested with 3 devices below and above the failure voltage to classify the part. The Pass/Fail status of a part is determined by the manufacturing test specification. The ESD class quoted indicates that the device passed exposure to a certain voltage, but does not pass the next higher level. The following table indicates the JESD ESD sensitivity classification levels.

Class	Passes	Fails
0	0 V	<250 V
1A	250 V	500 V
1B	500 V	1000 V
1C	1000 V	2000 V
2	2000 V	4000 V

Part Number	ESD Rating
SGA-5263Z	1B

#### **X. Operational Life Test Results** The results for SGA-5263Z High Temperature Operating Life Test are as follows

HTOL Completion Date	Test Duration	Junction Temperature	Quantity	Device Hours
June-04	1000 hours	150°C	80	80,000

Table 1: Summary of High Temperature Operational Life Test Cumulative Device Hours

XI. Qualification Test Results for SGA-5263Z					
Initial Qualification Date – July, 2004					
Group A0	Moisture preconditioning and three reflow cycles				
Test Conditions	Temperature = 270°C Peak, Slope < 6°C/second				
Number of Devices Under Test	210	Test Standard	JESD22- A113(C)	Results	PASS

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Group A1a	Temperature Cycling (Air to Air Thermal Shock) – Soldered on PCB					
Test Conditions	Temperature Range -65°C to 150°C, 10 min dwell, 1 minute transition, 1000 cycles					
Number of Devices Under Test	20	Test Standard	JESD22- A104(B)	Results	Pass	
Group A1b	Temperature	e Cycling (Air to	Air Thermal Shoc	k)		
Test Conditions	Temperature Range -65°C to 150°C, 10 min dwell, 1 minute transition, 1000 cycles					
Number of Devices Under Test	20	Test Standard	JESD22- A104(B)	Results	PASS	
Group A2	High Temperature Operating Life Test					
Test Conditions	Junction Terr	perature = 150°	C, Test Duration = 1	000 hours		
Number of Devices Under Test	80	Test Standard	JESD22- A108(B)	Results	PASS	
Group B	HAST					
Test Conditions	Temperature = 110°C, 85% Relative Humidity, Test Duration = 264 hours					
Number of Devices Under Test	15	Test Standard	JESD22- A110(B)	Results	PASS	
Group C	Autoclave					
Test Conditions	Temperature = 121°C, Relative Humidity = 100%, Test Duration = 96 hours					
Number of Devices Under Test	40	Test Standard	JESD22- A102(C)	Results	PASS	





Group D	Power Temperature Cycle					
Test Conditions	Temperature = -40°C to 85°C, Asynchronous bias, Test Duration = 168 hours					
Number of Devices Under Test	20	Test Standard	JESD22- A109(A)	Results	PASS	
Group E	High Tempe	rature Storage				
Test Conditions	Temperature	Temperature = 150°C, Test Duration = 1000 hours				
Number of Devices Under Test	20	Test Standard	JESD22- A103(B)	Results	PASS	
Group F	Low Temperature Storage					
Test Conditions	Temperature = -40°C, Test Duration = 1000 hours					
Number of Devices Under Test	20	Test Standard	SMDI Internal	Results	PASS	
Group G	Solderability	Solderability Steam Age				
Test Conditions	Temperature = 245°C, Test Duration = 60 seconds					
Number of Devices Under Test	15	Test Standard	JESD22- B102(C) Condition B	Results	PASS	
Group I	Tin Whiskering Unbiased					
Test Conditions	Temperature 51°C/85% humidity. Test Duration 1000 hours.					
Number of Devices Under Test	10	Test Standard	SMDI Internal	Results	PASS	





#### XII. Junction Temperature Determination

One key issue in performing qualification testing is to accurately determine the junction temperature of the device. Sirenza Microdevices uses a 3um spot size emissivity corrected infrared camera measurement to resolve the surface temperature of the device at the maximum operational power dissipation. The results are displayed below for the device running at operational current of 60.9 mA, a device voltage of 3.18 V, and a lead temperature of 87.7°C.





#### XIV. Junction Temperature Determination of SGA-8343Z

One key issue in performing qualification testing is to accurately determine the junction temperature of the device. Sirenza Microdevices uses a 3um spot size emissivity corrected infrared camera measurement to resolve the surface temperature of the device at the maximum operational power dissipation. The results are displayed below for the device running at operational current of 50.0mA, a device voltage of 4V, and a lead temperature of 85.1°C.



